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## Wide Bandgap Semiconductor Based Solar-Blind Photodetectors

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## Message from the Guest Editors

Wide bandgap semiconductors—including Al<sub>x</sub>Ga<sub>1-x</sub>N, Ga<sub>2</sub>O<sub>3</sub>, BN, Mg<sub>x</sub>Zn<sub>1-x</sub>O, and diamond—have attracted increasing interest over the last decade both from academia and industry. These materials have given rise to numerous disruptive applications such as ultraviolet (UV) light emitting diodes, UV lasers, power rectifiers and power field effect transistors. In contrast, applications involving the detection of UV light have received much less attention. The recent emergence of new wide bandgap semiconductors such as Ga<sub>2</sub>O<sub>3</sub> polymorphs has sparked renewed interest for UV sensing, in particular in the solarblind region.

Accordingly, this Special Issue will showcase the latest advances in solar-blind photodetectors based on wide bandgap semiconductors and will cover aspects of material synthesis and device processing, structural and optoelectronic properties of photodetectors, material and device modelling, to name a few.

- Ultraviolet photodetectors
- Wide bandgap semiconductors: AlxGa1-xN, Ga2O3, BN, MgxZn1-xO, Diamond

We look forward to receiving your submissions!



